

isc Silicon PNP Darlington Power Transistor

ISC2650

DESCRIPTION

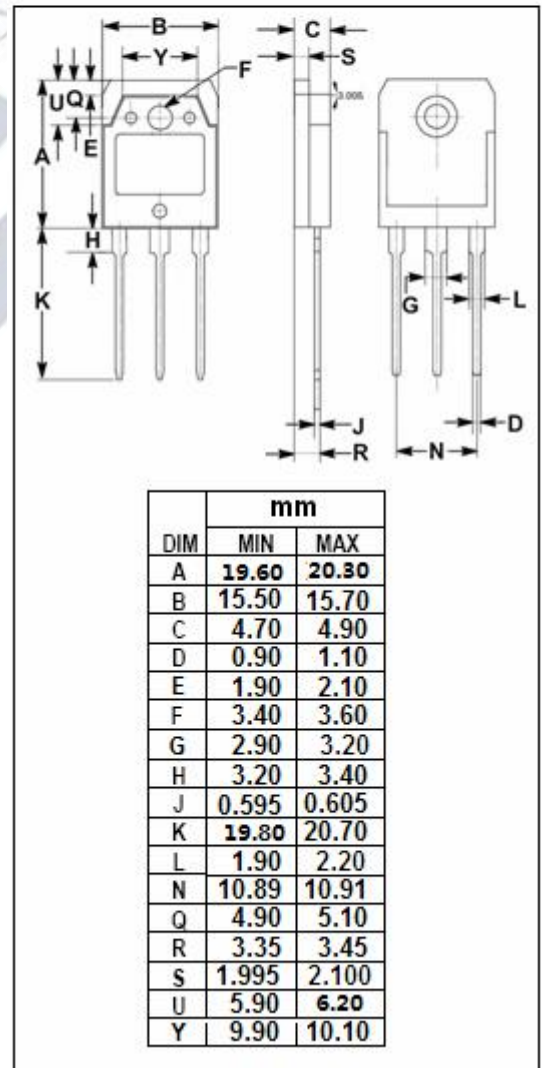
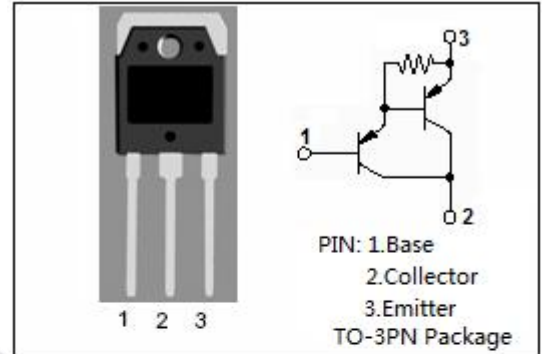
- High DC Current Gain-
: $h_{FE} = 5000(\text{Min}) @ I_C = -6\text{A}$
- Low-Collector Saturation Voltage-
: $V_{CE(\text{sat})} = -2.5\text{V}(\text{Max.}) @ I_C = -6\text{A}$
- Complement to Type ISC2649

APPLICATIONS

- Designed for audio, series regulator and general purpose applications.

ABSOLUTE MAXIMUM RATINGS($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-200	V
V_{CEO}	Collector-Emitter Voltage	-200	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-15	A
I_B	Base Current- Continuous	-1	A
P_C	Collector Power Dissipation @ $T_C = 25^\circ\text{C}$	130	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



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ELECTRICAL CHARACTERISTICS

 T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -30mA; I _B = 0	-200			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -10A; I _B = -10mA			-2.5	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -10A; I _B = -10mA			-3.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -200V; I _E = 0			-100	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -5V; I _C = 0			-100	μ A
h _{FE}	DC Current Gain	I _C = -10A; V _{CE} = -4V	5000			
f _T	Current-Gain—Bandwidth Product	I _E = 2A; V _{CE} = -12V		70		MHz